



# FQB34P10TM\_F085 Information



For Reference Only

Part Number FQB34P10TM\_F085

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

MOSFETT P. CHARON 22.5 A. POPLAY

**Description** MOSFET P-CH 100V 33.5A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## FQB34P10TM\_F085 Specifications

Manufacturer Part Number         FQB34P10TM_F085           Manufacturer         Fairchild/ON Semiconductor           Category         Discrete Semiconductor Products           Package         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB           Series         Automotive, AEC-Q101, QFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         33.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         2910pF @ 25V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         3.75w (Ta), 155w (Tc)           Rds On (Max) @ Id, Vgs         60 mOhm @ 16.75A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         D2PAK (TO-263AB)           Package / Case         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesAutomotive, AEC-Q101, QFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C33.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2910pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)3.75W (Ta), 155W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16.75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK (TO-263AB)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer Part Number	FQB34P10TM_F085
Package         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB           Series         Automotive, AEC-Q101, QFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         33.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         110nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         2910pF @ 25V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         3.75W (Ta), 155W (Tc)           Rds On (Max) @ Id, Vgs         60 mOhm @ 16.75A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         D2PAK (TO-263AB)           Package / Case         TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer	Fairchild/ON Semiconductor
Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series Automotive, AEC-Q101, QFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 33.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2910pF @ 25V Vgs (Max)  FET Feature - Power Dissipation (Max) 3.75W (Ta), 155W (Tc) Rds On (Max) @ Id, Vgs 60 mOhm @ 16.75A, 10V Operating Temperature Surface Mount Supplier Device Package D2PAK (TO-263AB) Package / Case	Category	Discrete Semiconductor Products
SeriesAutomotive, AEC-Q101, QFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C33.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2910pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)3.75W (Ta), 155W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16.75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK (TO-263AB)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB		Transistors - FETs, MOSFETs - Single
FET Type P-Channel MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 33.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2910pF @ 25V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 3.75W (Ta), 155W (Tc) Rds On (Max) @ Id, Vgs 60 mOhm @ 16.75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK (TO-263AB) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Technology Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 33.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2910pF @ 25V Vgs (Max) +25V FET Feature - Power Dissipation (Max) 3.75W (Ta), 155W (Tc) Rds On (Max) @ Id, Vgs 0perating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK (TO-263AB) Package / Case  MOSFET (Metal Oxide) 100V 000 3.55 (Tc)	Series	Automotive, AEC-Q101, QFET?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C33.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2910pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)3.75W (Ta), 155W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16.75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK (TO-263AB)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  -  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  60 mOhm @ 16.75A, 10V  Operating Temperature  Surplier Device Package  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  60 mOhm @ 16.75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id       4V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       110nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       2910pF @ 25V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       3.75W (Ta), 155W (Tc)         Rds On (Max) @ Id, Vgs       60 mOhm @ 16.75A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       D2PAK (TO-263AB)         Package / Case       TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	33.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  2910pF @ 25V  Vgs (Max)  ±25V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  60 mOhm @ 16.75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  2910pF @ 25V  Vgs (Max)  EET Feature  - Power Dissipation (Max)  3.75W (Ta), 155W (Tc)  Rds On (Max) @ Id, Vgs  60 mOhm @ 16.75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)3.75W (Ta), 155W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16.75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAK (TO-263AB)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
FET Feature  Power Dissipation (Max)  3.75W (Ta), 155W (Tc)  Rds On (Max) @ Id, Vgs  60 mOhm @ 16.75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	2910pF @ 25V
Power Dissipation (Max)  3.75W (Ta), 155W (Tc)  60 mOhm @ 16.75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs  60 mOhm @ 16.75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	3.75W (Ta), 155W (Tc)
Mounting Type Surface Mount  Supplier Device Package D2PAK (TO-263AB)  Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	60 mOhm @ 16.75A, 10V
Supplier Device Package  D2PAK (TO-263AB)  Package / Case  TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	D2PAK (TO-263AB)
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

### FQB34P10TM\_F085 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### FQB34P10TM\_F085 Payment Methods



















## FQB34P10TM\_F085 Shipping Methods













If you have any question about FQB34P10TM\_F085, please do not hesitate to contact us!

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